

| | Hits | Search Text | DBs |
|---|------|---|--|
| 6 | 76 | ((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4) same (expos\$4 or illuminat\$4 or irradiat\$4)) and (post\$8imag\$4 or post\$5expos\$3) and (etch\$4 or RIE or (dry near5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask) same (post\$4etch\$4 or etch\$3 or RIE or (dry near4 etch\$4))) and ((expos\$4 or irradiat\$4 or illuminat\$4 or imag\$4) same (etch\$4 or RIE or post\$8etch) same (resist or photoresist) same (mask or pattern)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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| 7 | 11 | ((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4 or etch\$4) same (expos\$4 or illuminat\$4 or irradiat\$4)) and (post\$12imag\$4 or post\$9expos\$3) and (etch\$4 or RIE or (dry near\$5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near\$6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask) same (post\$4etch\$4 or etch\$3 or RIE or (dry near\$4 etch\$4))) and ((expos\$4 or irradiat\$4 or illuminat\$4 or imag\$4) same (etch\$4 or RIE or post\$8etch) same (resist or photoresist) same (mask or pattern)) and ash\$4 and strip\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 8 | 11 | ((post\$3imag\$4 or post\$2expos\$3 or ((expos\$4 or irradiat\$4 or illuminat\$4) near\$16 (repeat\$4 or post) near\$16 (resist or photoresist) near\$12 pattern)) same ((subsequent or after or follow\$3) near\$9 etch\$4) near\$12 (metal\$3 or gate or insulat\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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| 9 | 11 | ((post\$3imag\$4 or post\$2expos\$3 or ((expos\$4 or irradiat\$4 or illuminat\$4) near16 (repeat\$4 or post) near16 (resist or photoresist) near12 pattern)) same ((subsequent or after or follow\$3) near9 (etch\$4 or RIE)) near12 (metal\$3 or gate or insulat\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 10 | 15 | ((post\$3imag\$4 or post\$2expos\$3 or ((expos\$4 or irradiat\$4 or illuminat\$4) near16 (repeat\$4 or post or unprocessed or deteriorated or residu\$4) near16 (resist or photoresist) near5 pattern)) same ((subsequent or after or follow\$3) near9 (etch\$4 or RIE)) near12 (metal\$3 or gate or insulat\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 11 | 52 | 430/328.ccls. and ((expos\$4 or post\$4imag\$4 or post\$4irradiat\$4 or post\$4expos\$4) same (resist or photoresist) same pattern\$3 same (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying) same (after or subsequent\$4 or sequential\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 12 | 23 | 430/328.ccls. and (((expos\$4 or post\$4imag\$4 or post\$4irradiat\$4 or post\$4expos\$4) near12 (resist or photoresist) near9 pattern\$3) same (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying) same (after or subsequent\$4 or sequential\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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| 13 | 5 | 430/328.ccls. and (((post\$4imag\$4 or ((post\$4 or after or subsequent) near9 (irradiat\$4 or expos\$4))) near12 (resist or photoresist) near9 pattern\$3) same (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying) same (after or subsequent\$4 or sequential\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 14 | 293 | ((post\$4imag\$4 or ((post\$4 or subsequent\$3) near9 (irradiat\$4 or expos\$4))) near12 (resist or photoresist) near6 pattern\$3) near16 (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 15 | 123 | ((post\$4imag\$4 or ((post\$4 or subsequent\$3) near9 (irradiat\$4 or expos\$4))) near12 (resist or photoresist) near6 pattern\$3) near16 (post\$4etch or etch\$4 or RIE) near16 (metal\$4 or gate)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 16 | 123 | S16 NOT S14 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 17 | 34 | S16 NOT S14 and ((resist or photoresist) same (thin\$4 or residu\$4) same (etch\$3 or post\$4etch\$4) same (expos\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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| 18 | 2 | ((resist or photoresist) near6 pattern\$4) same (thin\$4 or residu\$4) same (etch\$3 or post\$4etch\$4) same (subsequent\$4 near9 expos\$4) same (remov\$4 or strip\$4)) and ((metal\$4 or underlayer or gate) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE)) and (((resist or photoresist) near9 pattern\$3) same (post\$4expos\$4 or post\$4irradiat\$4 or post\$4illuminat\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 19 | 57 | ((resist or photoresist) near6 pattern\$4) same (thin\$4 or residu\$4) same (etch\$3 or post\$4etch\$4) same (subsequent\$4 near9 expos\$4) same (remov\$4 or strip\$4)) and ((metal\$4 or underlayer or gate) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE)) and (((resist or photoresist) near4 pattern\$3) same (contact\$4 or treat\$4) same (expos\$4 or UV or irradiation or radiation) same ((post\$4treat\$\$ or post\$4expos\$4 or subsequent\$4) near9 (illumination or expos\$4))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 22 | 73 | ((resist or photoresist) near6 pattern\$4) same (thin\$4 or residu\$4) same ((subsequent\$4 or post\$3) near9 (expos\$4 or irradiat\$4 or UV or illuminat\$4)) same strip\$4 same etch\$4) and ((metal\$4 or underl\$4 or gate or conductive or electrode) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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| 23 | 54 | S23 NOT S20 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 24 | 14 | ((resist or photoresist) near16 pattern\$4) and post\$3imag\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 25 | 2 | ((resist or photoresist) near6 pattern\$4) and post\$3imag\$4 and (strip\$4 same etch\$4) and ((metal\$4 or underl\$4 or gate or conductive or electrode) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 26 | 102 | ((resist or photoresist) near16 pattern\$4) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illumiant\$4) near12 strip\$4 near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 27 | 42 | ((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illumiant\$4) near12 strip\$4 near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4)) same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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| 28 | 3 | ((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminant\$4) near12 (strip\$4 or remov\$4) near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4) near9 (UV or i\$4line or g\$3line or KrF or ArF or EUV or X\$2ray)) same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 29 | 3 | ((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminant\$4 or contact\$4 or treat\$4) near12 (strip\$4 or remov\$4) near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4) near9 (UV or i\$4line or g\$3line or KrF or ArF or EUV or X\$2ray)) same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 30 | 10 | ((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminant\$4 or contact\$4 or treat\$4) near12 (strip\$4 or remov\$4) near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4) near9 (UV or i\$4line or g\$3line or KrF or ArF or EUV or X\$2ray))) and ((resist or photoresist) same pattern same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |